

## PNP HDTV video transistor

T-33-17

BFQ290

PHILIPS INTERNATIONAL

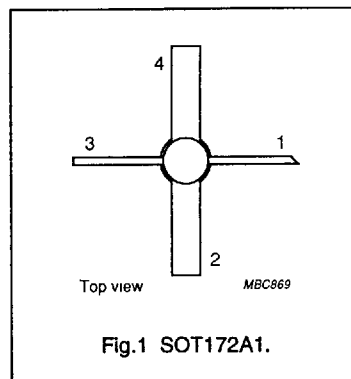
56E D ■ 7110826 0045673 597 ■ PHIN

## FEATURES

- High breakdown voltages
- Low output capacitance
- High gain bandwidth product
- Good thermal stability
- Gold metallization ensures excellent reliability
- Complementary NPN type BFQ291.

## PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | collector   |
| 2   | base        |
| 3   | emitter     |
| 4   | base        |



## DESCRIPTION

The BFQ290 has a 4-lead SOT172A1 stud envelope with a ceramic cap. All leads are isolated from the flange.

## LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

| SYMBOL     | PARAMETER                        | MIN. | MAX. | UNIT |
|------------|----------------------------------|------|------|------|
| $-V_{CBO}$ | collector-base voltage           | —    | 230  | V    |
| $-V_{CER}$ | collector-emitter voltage        | —    | 225  | V    |
| $-I_C$     | collector current                | —    | 250  | mA   |
| $P_{tot}$  | total power dissipation (note 1) | —    | 4    | W    |
| $T_J$      | junction temperature             | —    | 200  | °C   |

## Note

1.  $T_{mb} = 100\text{ °C}$ .

## CHARACTERISTICS

$T_J = 25\text{ °C}$  unless otherwise specified.

| SYMBOL         | PARAMETER                           | CONDITIONS                                                             | MIN. | TYP. | UNIT |
|----------------|-------------------------------------|------------------------------------------------------------------------|------|------|------|
| $-V_{(BR)CBO}$ | collector-base breakdown voltage    | open emitter; $-I_C = 100\text{ }\mu\text{A}$                          | 195  | —    | V    |
| $-V_{(BR)CER}$ | collector-emitter breakdown voltage | $-I_C = 1\text{ mA}$ ; $R_{BE} = 100\text{ }\Omega$                    | 190  | —    | V    |
| $h_{FE}$       | DC current gain                     | $-I_C = 25\text{ mA}$ ; $-V_{CE} = 10\text{ V}$                        | 15   | —    |      |
| $f_T$          | transition frequency                | $-I_C = 25\text{ mA}$ ; $-V_{CE} = 10\text{ V}$ ; $f = 100\text{ MHz}$ | 400  | —    | MHz  |
| $C_{cb}$       | collector-base capacitance          | $I_C = I_b = 0$ ; $-V_{CB} = 10\text{ V}$ ; $f = 1\text{ MHz}$         | —    | 1.8  | pF   |